



PRELIMINARY

SFT5321/23-28D

SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada, CA 90638
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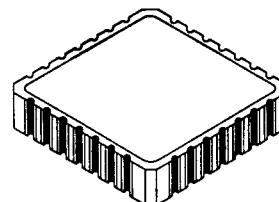
Designer's Data Sheet

FEATURES:

- Radiation Tolerant
- Eutectic Die Attach
- Hermetic Package
- TX, TXV and Space Levels Available

**2 AMP NPN - 2 AMP PNP
75 VOLT NPN - 75 VOLT PNP
NPN AND PNP BIPOLAR
COMPLEMENTARY TRANSISTOR**

28 PIN CLCC



MAXIMUM RATINGS CHARACTERISTIC	SYMBOL	VALUE		UNIT
		NPN	PNP	
Collector-Emitter Voltage	V _{CEO}	50	50	V
Collector-Base Voltage	V _{CBO}	75	75	V
Emitter-Base Voltage	V _{EBO}	5	5	V
Collector Current	I _C	2	2	A
Base Current	I _B	1.0	1.0	A
Total Device Dissipation @ TC= 25°C, Each die	P _D	7.8		W
Total Device Dissipation Derating, each die	P _D /T _{case}	.062		Watt/deg C
Operating and Storage Temperature	Top & Tstj	-55 to +150		°C
Thermal Resistance, Junction to Case, each die	R _{θJC}	16		°C/W

PACKAGE OUTLINE: 28 PIN CLCC

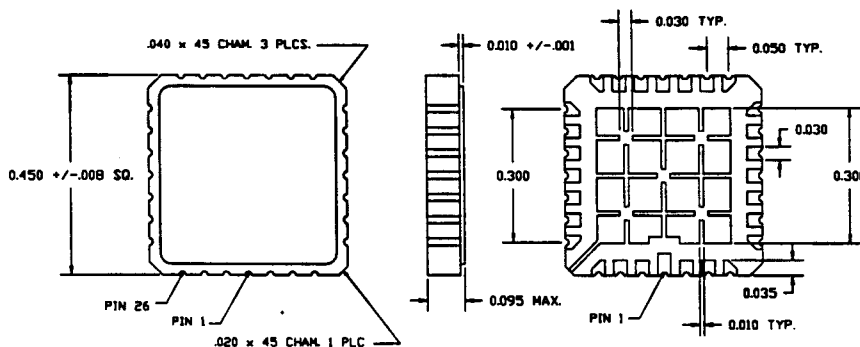
PIN OUT:

PNP:

PINS: 2-6 COLLECTOR
PINS: 8 BASE
PINS: 9-14 EMITTER

NPN:

PINS: 16-21 EMITTER
PINS: 22 BASE
PINS: 24-28 COLLECTOR



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: XP00010 A

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ELECTRICAL CHARACTERISTICS	SYMBOL	PNP		NPN		UNIT		
		MIN	MAX	MIN	MAX			
RATING								
Collector-Emitter Sustain Breakdown Voltage) (IC= .1A, IB= 0)	BVCEO	50		50		V		
Collector Cutoff Current (VCE=75V, VBE (off) = 1.5V)	ICEX		100		100	uA		
(VCE= 45V, VBE(off)= 1.5V, 150 deg.C)	ICEX		5		5	mA		
Emitter Cutoff Current NPN and PNP:(VEB = 5 Vdc)	IEBO		100		100	uA		
DC Current Gain IC= 0.5 Adc, VCE=4 Vdc	HFE	40	300	40	250			
Collector -Emitter Saturation Voltage (IC=500mA, IB =50mA)	VCE(SAT)		1.2		0.8	V		
Base-Emitter Voltage, VBE (VCE= 4V, IC=500mA)	VBE(ON)		1.4		1.4	V		
Common-Emitter Small-Signal-Circuit Foward_circuit Transfer ratio (VCE= 4V, IC= 50mA, f=10MHz)	hfe1	5		5				
Delay Time Rise Time	ton	VCC= 30 Vdc IC= 500 mAdc IB1=IB2=50mA			100		80	nsec
Storage Time Fall Time					1000		800	nsec

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.